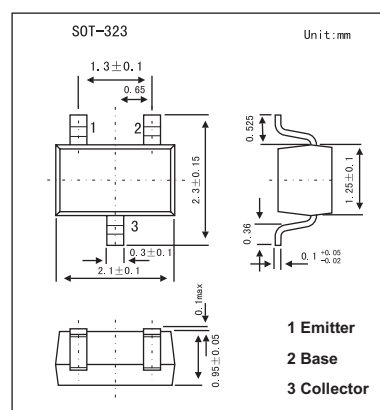


Silicon PNP Epitaxial

2SA1587

■ Features

- High voltage $V_{CEO} = -120V$
- High h_{FE} $h_{FE} = 200$ to 700
- Low noise
- Small package

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-120	V
Emitter-base voltage	V_{EBO}	-120	V
Collector-emitter voltage	V_{CEO}	-5	V
Collector current	I_C	-100	mA
Base current	I_B	-20	mA
Collector power dissipation	P_C	100	mW
Junction temperature	T_j	125	$^\circ C$
Storage temperature range	T_{stg}	-55 to +125	$^\circ C$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = -120 V, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5 V, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -6 V, I_C = -2 mA$	200		700	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10 mA, I_B = -1 mA$			0.3	V
Transition frequency	f_T	$V_{CE} = -6 V, I_E = 1 mA$		100		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10 V, I_E = 0, f = 1 MHz$		4		pF
Noise figure	NF	$V_{CE} = -6 V, I_C = -0.1 mA, f = 1 kHz, R_g = 10 K\Omega$		1.0	10	dB

■ h_{FE} Classification

Marking	CG	CL
Rank	GR	BL
h_{FE}	200~400	350~700